Ann Arbor, MI

Expected: 2025

# BIOGRAPHY

Wenhao Peng was born in Shanghai, China, in 1995. He received the B.S.E. degree in ECE from Shanghai Jiao Tong University, Shanghai, in 2018, the B.S.E. degree in EE from the University of Michigan, Ann Arbor, MI, USA, in 2018, the M.S. degree in ECE from the University of Michigan, in 2019, and the M.S.E. degree in ME from the University of Michigan, in 2024, where he is currently pursuing the Ph.D. degree in electrical and computer engineering. His research interests include designing and modeling acoustic wave resonators driven by thin-film piezoelectric and ferroelectric materials for applications in frontend filters and developing fabrication technologies for resonant MEMS devices.

# EDUCATION

#### The University of Michigan

Electrical and Computer Engineering PhD, 4.00/4.00

Acoustic Wave Resonators, Thin Film Ferroelectrics, Resonant MEMS Fabrication. Aluminum Nitride, Scandium Aluminum Nitride, and Barium Strontium Titanate based devices. Cleanroom device fabrication and mm-wave frequency network analyzer measurements. Theory and finite element simulations. Develop novel acoustic wave resonators that operate at mm-wave frequencies with record-setting performance based on the knowledge background in electrical and computer engineering and mechanical engineering.

The University of Michigan	Ann Arbor, MI
Master of Science in Engineering, Mechanical Engineering, 4.00/4.00	Received in 2024
The University of Michigan	Ann Arbor, MI
Master of Science, Electrical and Computer Engineering, 4.00/4.00	Received in 2019
The University of Michigan	Ann Arbor, MI
Bachelor of Science in Engineering, Electrical E, Summa Cum Laude, 4.00/4.00	Received in 2018
Shanghai Jiao Tong University	Shanghai, China
Bachelor of Science in Engineering, Electrical and Computer Engineering	Received in 2018

### PUBLICATIONS

W. Peng, S. Nam, D. Wang, Z. Mi, and A. Mortazawi, "A 36 GHz Trilayer AlN/ScAlN/AlN Periodically Poled FBAR," accepted to 2025 IEEE/MTT-S International Microwave Symposium.

H. Desai, **W. Peng** and A. Mortazawi, "Single-Pole Single-Throw RF Acoustic Phase Inversion Switch Leveraging Poled Ferroelectrics," in *IEEE Transactions on Microwave Theory and Techniques*, vol. 73, no. 1, pp. 6-13, Jan. 2025,

doi: 10.1109/TMTT.2024.3496665.

W. Peng, S. Nam, D. Wang, Z. Mi, and A. Mortazawi, "A 56 GHz Trilayer AlN/ScAlN/AlN Periodically Poled FBAR," 2024 IEEE/MTT-S International Microwave Symposium - IMS 2024, Washington, DC, USA, 2024, pp. 150-153,

doi: 10.1109/IMS40175.2024.10600386.

D. Wang, P. Wang, S. Mondal, J. Liu, M. Hu, M. He, S. Nam, **W. Peng**, S. Yang, D. Wang, Y. Xiao, Y. Wu, A. Mortazawi, and Z. Mi, "Controlled ferroelectric switching in ultrawide bandgap AlN/ScAlN multilayers," *Applied Physics Letters*, vol. 123, no. 10, p. 103506, 09 2023,

doi: 10.1063/5.0160163

S. Nam, W. Peng, P. Wang, D. Wang, Z. Mi, and A. Mortazawi, "A mm-Wave Trilayer AlN/ScAlN/AlN Higher Order Mode FBAR," in *IEEE Microwave and Wireless Technology Letters*, vol. 33, no. 6, pp. 803-806, June 2023, doi: 10.1109/LMWT.2023.3271865.

W. Peng, M. Z. Koohi, S. Nam, and A. Mortazawi, "Phenomenological Circuit Modeling of Ferroelectric-Driven Bulk Acoustic Wave Resonators," in *IEEE Transactions on Microwave Theory and Techniques*, vol. 70, no. 1, pp. 919-925, Jan. 2022,

doi: 10.1109/TMTT.2021.3130609.

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W. Peng, M. Z. Koohi, S. Nam, and A. Mortazawi, "Physics Based Modeling of Electrostriction Based BAW Resonators," 2021 IEEE MTT-S International Microwave Symposium (IMS), Atlanta, GA, USA, 2021, pp. 214-217, doi: 10.1109/IMS19712.2021.9574949.

S. Nam, M. Z. Koohi, **W. Peng**, and A. Mortazawi, "A Switchless Quad Band Filter Bank Based on Ferroelectric BST FBARs," in *IEEE Microwave and Wireless Components Letters*, vol. 31, no. 6, pp. 662-665, June 2021, doi: 10.1109/LMWC.2021.3069880.

M. Z. Koohi, **W. Peng**, and A. Mortazawi, "An Intrinsically Switchable Balanced Ferroelectric FBAR Filter at 2 GHz," 2020 IEEE/MTT-S International Microwave Symposium (IMS), Los Angeles, CA, USA, 2020, pp. 131-134, doi: 10.1109/IMS30576.2020.9223799.

Y. Dai, W. Peng, Y. Wang, L.-X. Chuo, K. Suri, H. Zheng, D. Wentzloff, and H.-S. Kim, "Implementation and evaluation of bi-directional wifi back-channel communication," in 2018 IEEE 29th Annual International Symposium on Personal, Indoor and Mobile Radio Communications (PIMRC), Bologna, Italy, 2018, pp. 1–7, doi: 10.1109/PIMRC.2018.8580736.

### COURSEWORK

MECHENG 645 Wave Propagation in Elastic Solids MECHENG 641 Advanced Vibrations of Structures MECHENG 541 Mechanical Vibrations MECHENG 524 Advanced Engineering Acoustics MECHENG 511 Theory of Solid Continua MECHENG 501 Math Methods in ME MECHENG 424 Engineering Acoustics ROB 501 Math for Robotics EECS 530 Electromagnetic Theory I EECS 470 Computer Architecture EECS 455 Digital Communication Signals EECS 427 VLSI Design I EECS 414 Introduction to MEMS EECS 413 Monolithic Amplifier Circuits Ve 475 Introduction to Cryptography Ve 438 Advanded Lasers and Optics Laboratory EECS 311 Analog Circuits EECS 312 Digital Integrated Circuits EECS 330 Intro. to Antennas and Wireless Systems EECS 334 Principles of Optics EECS 351 Intro. to Digital Signal Processing EECS 370 Intro. to Computer Organization Vp 390 Modern Physics EECS 281 Data Structures and Algorithms

Ve 230 Electromagnetics I Ve 280 Programming & Elem. Data Structures Vp 260 Honors Physics II Vp 141 Physics Lab I Vp 241 Physics Lab II Vc 210 Chemistry EECS 627 VLSI Design II EECS 525 Advanced Solid-State Microwave Circuits EECS 522 Analog Integrated Circuits EECS 452 DSP Design Lab EECS 411 Microwave Circuits I Ve 401 Probabilistic Methods in Engineering EECS 320 Intro. to Semiconductor Devices Ve 203 Discrete Mathematics Ve 215 Intro. to Circuits Ve 216 Intro. to Signals and Systems Ve 270 Intro. to Logic Design Vv 286 Honors Mathematics IV Vv 285 Honors Mathematics III Vv 186 Honors Mathematics II Vp 160 Honors Physics I Vg 101 Intro. to Computers & Programming Vc 211 Chemistry Lab Vg 100 Intro. to Engineering

Note:  $\mathbf{A}$ + grades are received where class numbers are bold.

### TEACHING ASSISTANCE

EECS 411 Microwave Circuits I F19,F20,F21 EECS 312 Digital ICs W21,F22,W24,F24,W25 EECS 215 Intro to Elect Circ W22,W23,F23,S24 Vp 160 Honors Physics I S16,S18 Vc 211 Chemistry Lab S16 Vc 210 Chemistry F15